ALPHA & OMEGA SEMICONDUCTOR

AO4449

30V P-Channel MOSFET

General Description

The AO4449 uses advanced trench technology to provide excellent RDS(ON), and ultra-low low gate charge. This device is suitable for use as a load switch or in PWM applications.

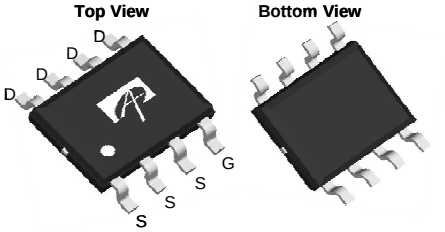
Product Summary

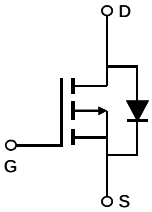
V_{DS}	-30V
I_D (at V_{GS}=-10V)	-7A
$R_{DS(ON)}$ (at V_{GS}=-10V)	< 34mΩ
$R_{DS(ON)}$ (at V_{GS} = -4.5V)	< 54mΩ

100% UIS Tested
100% R_g Tested

Green Product

SOIC-8





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	-7	A
	T_A=70°C		-5.5	
Pulsed Drain Current [C]		I_{DM}	-40	
Avalanche Current [C]		I_{AS}, I_{AR}	23	A
Avalanche energy L=0.1mH [C]		E_{AS}, E_{AR}	26	mJ
Power Dissipation [B]	T_A=25°C	P_D	3.1	W
	T_A=70°C		2	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	31	40	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		59	75	°C/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	16	24	°C/W